



Rev. 1.1

UTRON

UT62L1024(I)

128K X 8 BIT LOW POWER CMOS SRAM

REVISION HISTORY

REVISION	DESCRIPTION	Date
Rev. 1.0	Original.	Mar. 27. 2003
Rev. 1.1	Add order information for lead free product	May. 09. 2003



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UT62L1024(I) 128K X 8 BIT LOW POWER CMOS SRAM

FEATURES

- Fast access time : 55/70ns
- CMOS low power operation
 - Operating current : 20/18/15mA (TYP.)
 - Standby current : 20 uA(TYP.) L-version
 - 2 uA(TYP.) LL-version
- Single 2.5V~3.6V power supply
- Operating temperature:
 - Industrial : -40 ~85
- All TTL compatible inputs and outputs
- Fully static operation
- Three state outputs
- Data retention voltage: 1.5V (min)
- Package : 32-pin 450mil SOP
 - 32-pin 8mm x 20mm TSOP-
 - 32-pin 8mm x 13.4mm STSOP
 - 36-pin 6mm x 8mm TFBGA

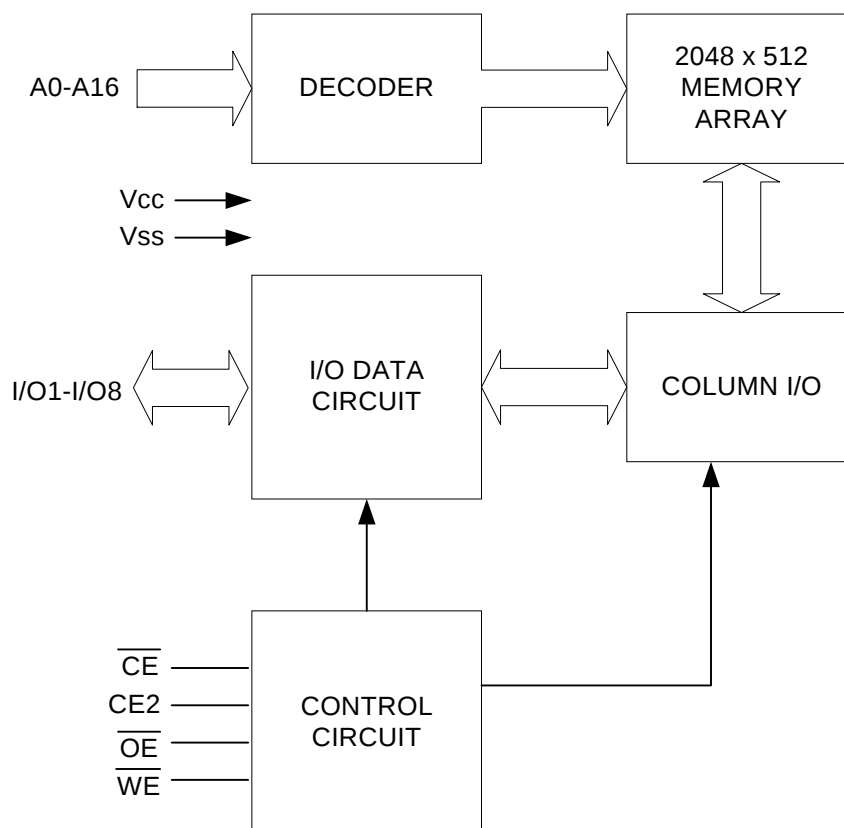
GENERAL DESCRIPTION

The UT62L1024(I) is a 1,048,576-bit low power CMOS static random access memory organized as 131,072 words by 8 bits. It is fabricated using high performance, high reliability CMOS technology.

The UT62L1024(I) is designed for very low power system applications. It is particularly well suited for battery back-up nonvolatile memory applications.

It operates from a wide range of 2.5V~ 3.6V supply voltage. Easy memory expansion is provided by using two chip enable input, $\overline{CE}$ & CE2. And all inputs and three-state outputs are fully TTL compatible.

FUNCTIONAL BLOCK DIAGRAM





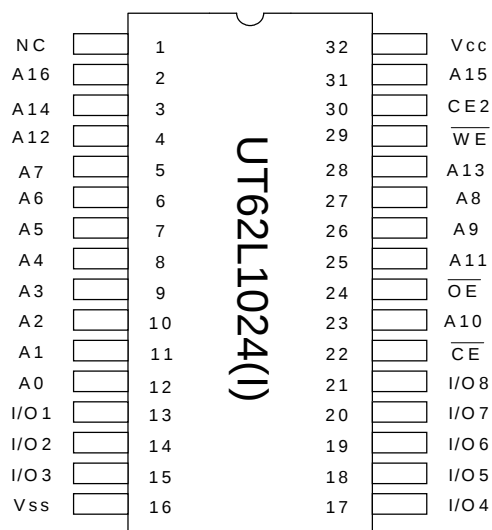
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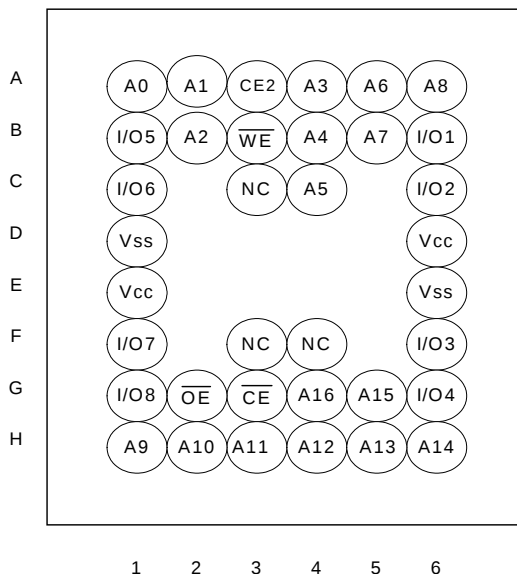
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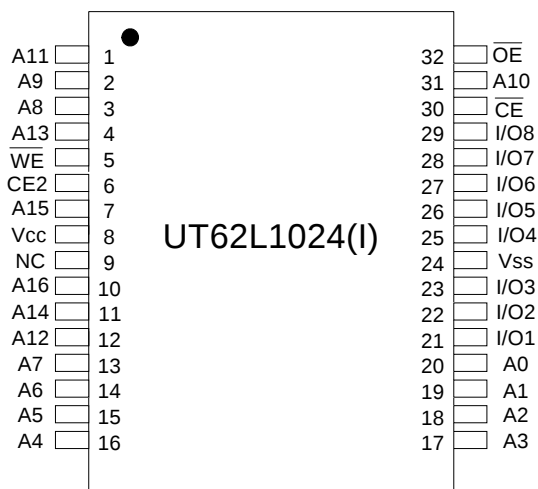
PIN CONFIGURATION



SOP



TFBGA



TSOP-1/STSOP

PIN DESCRIPTION

SYMBOL	DESCRIPTION
A0 - A16	Address Inputs
I/O1 - I/O8	Data Inputs/Outputs
CE, CE2	Chip Enable Inputs
WE	Write Enable Input
OE	Output Enable Input
Vcc	Power Supply
Vss	Ground
NC	No Connection



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TRUTH TABLE

MODE	$\overline{CE}$	CE2	$\overline{OE}$	$\overline{WE}$	I/O OPERATION	SUPPLY CURRENT
Standby	H	X	X	X	High - Z	I_{SB}, I_{SB1}
	X	L	X	X	High - Z	I_{SB}, I_{SB1}
Output Disable	L	H	H	H	High - Z	I_{CC}, I_{CC1}, I_{CC2}
Read	L	H	L	H	D_{OUT}	I_{CC}, I_{CC1}, I_{CC2}
Write	L	H	X	L	D_{IN}	I_{CC}, I_{CC1}, I_{CC2}

Note: H = V_{IH} , L = V_{IL} , X = Don't care.

ABSOLUTE MAXIMUM RATINGS*

PARAMETER	SYMBOL	RATING	UNIT
Terminal Voltage with Respect to V_{SS}	V_{TERM}	-0.5 to 4.6	V
Operating Temperature	T_A	-40 to 85	
Storage Temperature	T_{STG}	-65 to 150	
Power Dissipation	P_D	1	W
DC Output Current	I_{OUT}	50	mA
Soldering Temperature (under 10 secs)	T_{solder}	260	

*Stresses greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to the absolute maximum rating conditions for extended period may affect device reliability.

DC ELECTRICAL CHARACTERISTICS ($V_{CC} = 2.5V \sim 3.6V$, $T_A = -40$ to 85)

PARAMETER	SYMBOL	TEST CONDITION		MIN.	TYP.	MAX.	UNIT
Power Voltage	V _{CC}			2.5	3.0	3.6	V
Input High Voltage	V _{IH} ^{*1}			2.2	-	V _{CC} +0.3	V
Input Low Voltage	V _{IL} ^{*2}			- 0.2	-	0.6	V
Input Leakage Current	I _{LI}	V _{SS} V _{IN} V _{CC}		- 1	-	1	μA
Output Leakage Current	I _{LO}	V _{SS} V _{I/O} V _{CC} , Output Disabled		- 1	-	1	μA
Output High Voltage	V _{OH}	I _{OH} = - 1mA (I _{OH} = -0.5mA when V _{CC} <2.7V)		2.2	2.7	-	V
Output Low Voltage	V _{OL}	I _{OL} = 2.1mA		-	-	0.4	V
Operating Current	I _{CC}	Cycle time=Min.100% duty, CE =V _{IL} and CE2 = V _{IH} , I _{I/O} =0mA	55	-	20	35	mA
			70	-	18	30	mA
	I _{CC1}	100%duty, I _{I/O} =0mA, CE 0.2V and CE2 V _{CC} -0.2V, other pins at 0.2V or V _{CC} -0.2V	TCycle= 1μs	-	4	5	mA
	I _{CC2}		TCycle= 500ns	-	8	10	mA
Standby Current (TTL)	I _{SB}	CE =V _{IH} or CE2 = V _{IL}		-	0.3	0.5	mA
Standby Current (CMOS)	I _{SB1}	CE =V _{CC} -0.2V or CE2=0.2V, other pins at 0.2V or V _{CC} -0.2V	-L	-	20	80	μA
			-LL	-	2	10	μA

Notes:

1. Overshoot : $V_{CC}+3.0v$ for pulse width less than 10ns.
2. Undershoot : $V_{SS}-3.0v$ for pulse width less than 10ns.
3. Overshoot and Undershoot are sampled, not 100% tested.



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CAPACITANCE ($T_A=25^\circ\text{C}$, $f=1.0\text{MHz}$)

PARAMETER	SYMBOL	MIN.	MAX	UNIT
Input Capacitance	C_{IN}	-	6	pF
Input/Output Capacitance	$C_{I/O}$	-	8	pF

Note : These parameters are guaranteed by device characterization, but not production tested.

AC TEST CONDITIONS

Input Pulse Levels	$0.1V_{CC}$ to $0.9V_{CC}$
Input Rise and Fall Times	5ns
Input and Output Timing Reference Levels	1.5V
Output Load	$C_L = 30\text{pF} + 1\text{TTL}$, $I_{OH} = -1\text{mA}$, $I_{OL} = 2.1\text{mA}$

AC ELECTRICAL CHARACTERISTICS ($V_{CC} = 2.5\text{V} \sim 3.6\text{V}$, $T_A = -40^\circ\text{C}$ to 85°C)

(1) READ CYCLE

PARAMETER	SYMBOL	UT62L1024(I)-55		UT62L1024(I)-70		UNIT
		MIN.	MAX.	MIN.	MAX.	
Read Cycle Time	t_{RC}	55	-	70	-	ns
Address Access Time	t_{AA}	-	55	-	70	ns
Chip Enable Access Time	t_{ACE}	-	55	-	70	ns
Output Enable Access Time	t_{OE}	-	30	-	35	ns
Chip Enable to Output in Low Z	t_{CLZ^*}	10	-	10	-	ns
Output Enable to Output in Low Z	t_{OLZ^*}	5	-	5	-	ns
Chip Disable to Output in High Z	t_{CHZ^*}	-	20	-	25	ns
Output Disable to Output in High Z	t_{OHZ^*}	-	20	-	25	ns
Output Hold from Address Change	t_{OH}	10	-	10	-	ns

(2) WRITE CYCLE

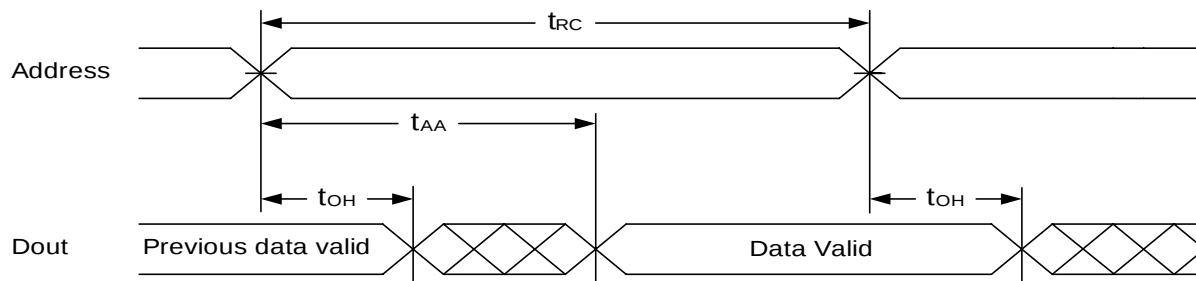
PARAMETER	SYMBOL	UT62L1024(I)-55		UT62L1024(I)-70		UNIT
		MIN.	MAX.	MIN.	MAX.	
Write Cycle Time	t_{WC}	55	-	70	-	ns
Address Valid to End of Write	t_{AW}	50	-	60	-	ns
Chip Enable to End of Write	t_{CW}	50	-	60	-	ns
Address Set-up Time	t_{AS}	0	-	0	-	ns
Write Pulse Width	t_{WP}	45	-	55	-	ns
Write Recovery Time	t_{WR}	0	-	0	-	ns
Data to Write Time Overlap	t_{DW}	25	-	30	-	ns
Data Hold from End of Write Time	t_{DH}	0	-	0	-	ns
Output Active from End of Write	t_{OW^*}	5	-	5	-	ns
Write to Output in High Z	t_{WHZ^*}	-	20	-	25	ns

*These parameters are guaranteed by device characterization, but not production tested.

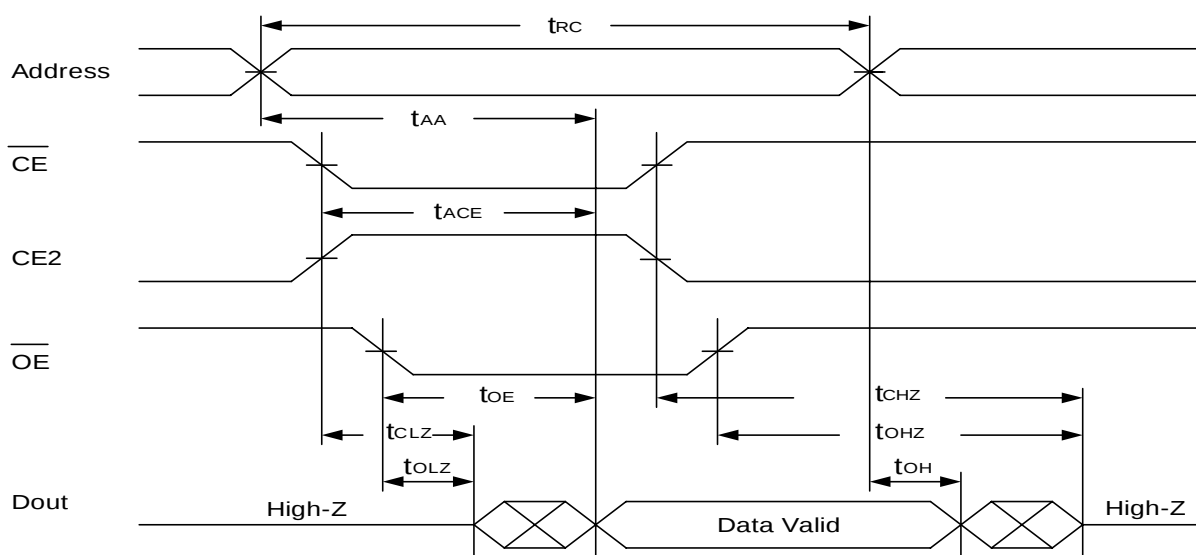


TIMING WAVEFORMS

READ CYCLE 1 (Address Controlled) (1,2)



READ CYCLE 2 ($\overline{CE}$ and CE2 and $\overline{OE}$ Controlled) (1,3,4,5)



Notes :

1. $\overline{WE}$ is high for read cycle.
2. Device is continuously selected $\overline{OE}$ =low, $\overline{CE}$ =low, CE2=high.
3. Address must be valid prior to or coincident with $\overline{CE}$ =low, CE2=high; otherwise t_{AA} is the limiting parameter.
4. t_{CLZ} , t_{OLZ} , t_{CHZ} and t_{OHZ} are specified with $C_L=5pF$. Transition is measured $\pm 500mV$ from steady state.
5. At any given temperature and voltage condition, t_{CHZ} is less than t_{CLZ} , t_{OHZ} is less than t_{OLZ} .



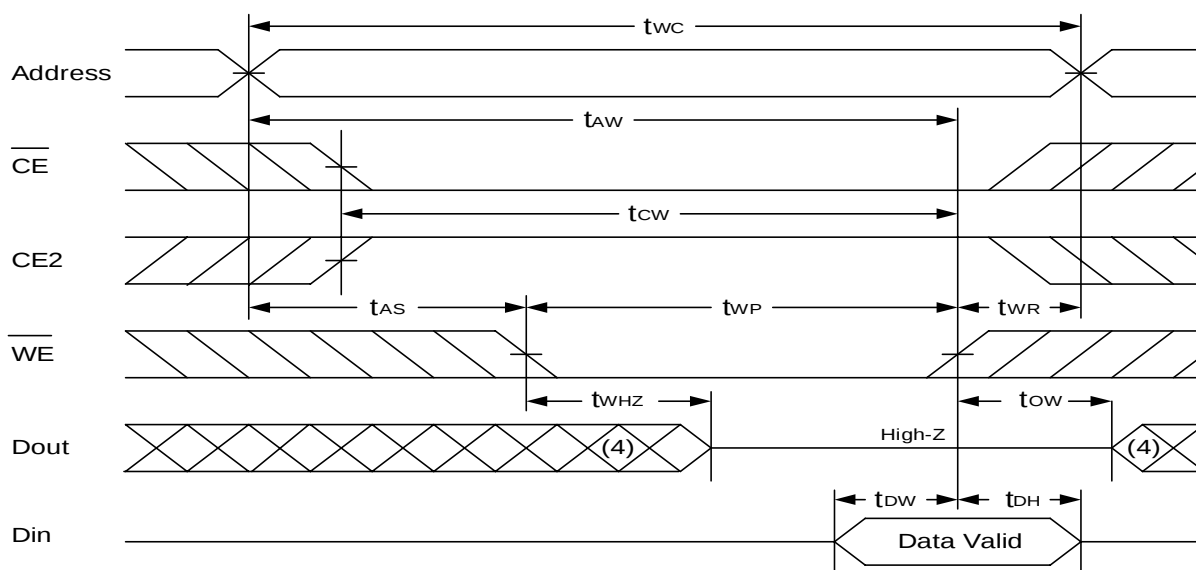
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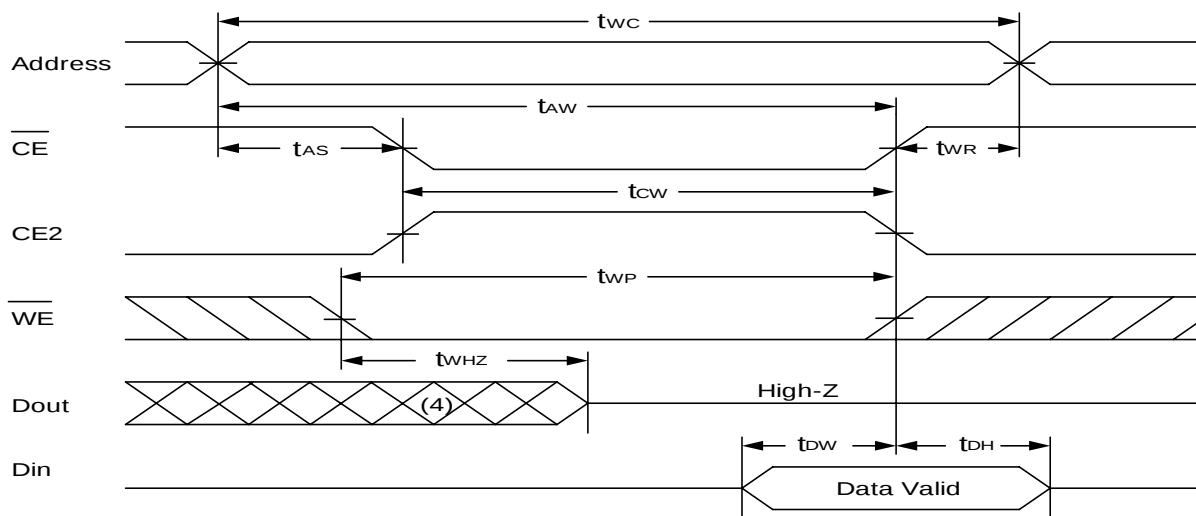
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WRITE CYCLE 1 ($\overline{WE}$ Controlled) (1,2,3,5,6)



WRITE CYCLE 2 ($\overline{CE}$ and CE2 Controlled) (1,2,5,6)



Notes :

1. $\overline{WE}$, $\overline{CE}$ must be high or CE2 must be low during all address transitions.
2. A write occurs during the overlap of a low $\overline{CE}$, high CE2, low $\overline{WE}$.
3. During a $\overline{WE}$ controlled write cycle with $\overline{OE}$ low, t_{WP} must be greater than $t_{WHZ} + t_{DW}$ to allow the drivers to turn off and data to be placed on the bus.
4. During this period, I/O pins are in the output state, and input signals must not be applied.
5. If the $\overline{CE}$ low transition and CE2 high transition occurs simultaneously with or after $\overline{WE}$ low transition, the outputs remain in a high impedance state.
6. t_{OW} and t_{WHZ} are specified with $C_L = 5pF$. Transition is measured $\pm 500mV$ from steady state.



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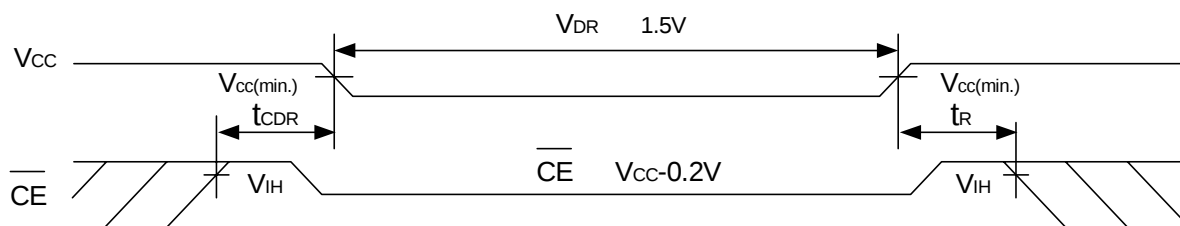
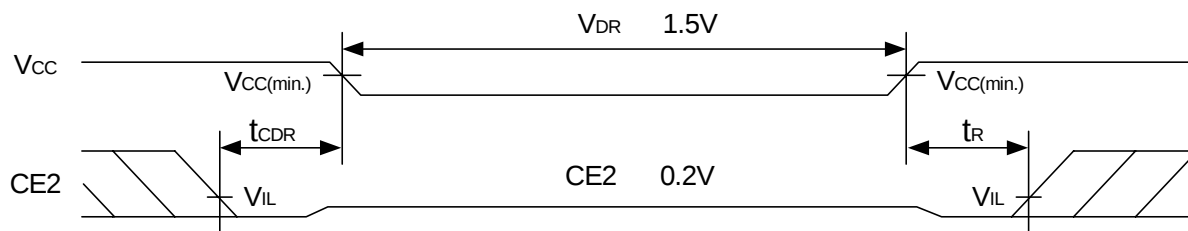
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DATA RETENTION CHARACTERISTICS ($T_A = -40$ to 85)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
V _{CC} for Data Retention	V _{DR}	$\overline{CE}$ V _{CC} -0.2V or CE2 0.2V	1.5	-	3.6	V
Data Retention Current	I _{DR}	V _{CC} =1.5V $\overline{CE}$ V _{CC} -0.2V or CE2 0.2V	- L	10	80	μ A
			- LL	1	6	μ A
Chip Disable to Data Retention Time	t _{CDR}	See Data Retention Waveforms (below)	0	-	-	ns
Recovery Time	t _R		t _{RC} *	-	-	ns

t_{RC}* = Read Cycle Time**DATA RETENTION WAVEFORM****Low V_{CC} Data Retention Waveform (1)** ($\overline{CE}$ controlled)**Low V_{CC} Data Retention Waveform (2)** (CE2 controlled)



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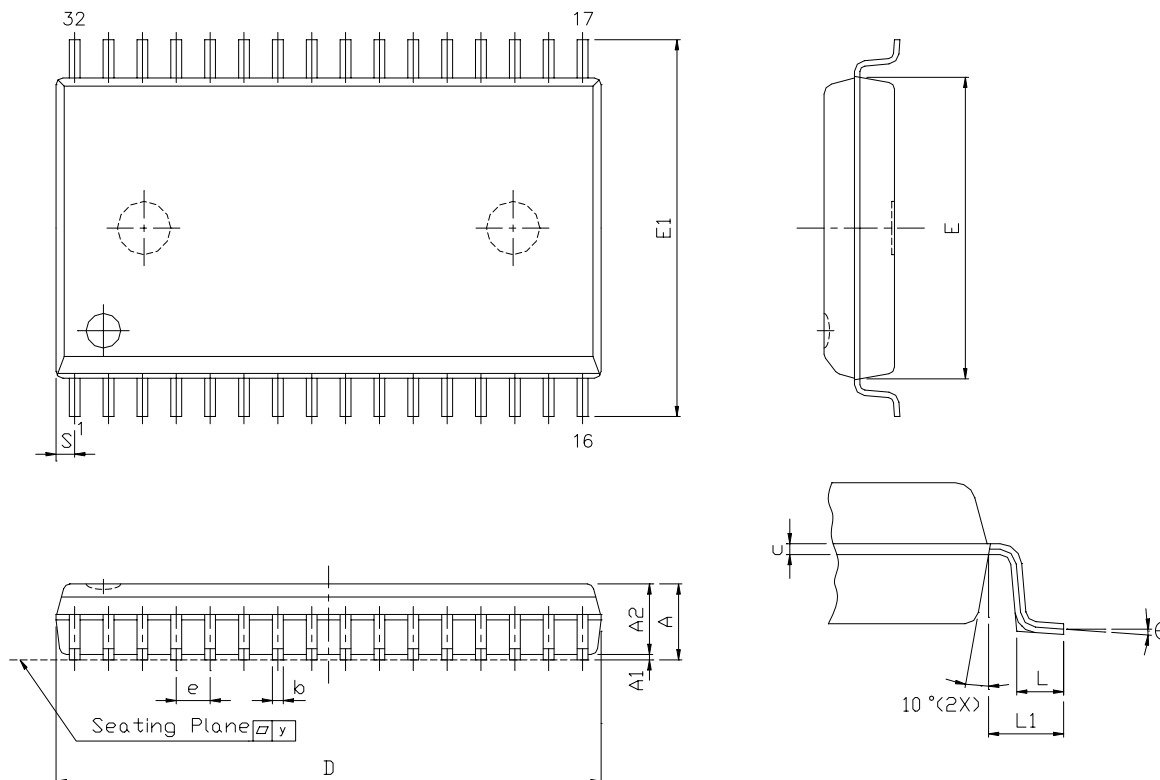
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PACKAGE OUTLINE DIMENSION

32 pin 450mil SOP Package Outline Dimension



UNIT SYMBOL	INCH(BASE)	MM(REF)
A	0.118 (MAX)	2.997 (MAX)
A1	0.004(MIN)	0.102(MIN)
A2	0.111(MAX)	2.82(MAX)
b	0.016(TYP)	0.406(TYP)
c	0.008(TYP)	0.203(TYP)
D	0.817(MAX)	20.75(MAX)
E	0.445 ±0.005	11.303 ±0.127
E1	0.555 ±0.012	14.097 ± 0.305
e	0.050(TYP)	1.270(TYP)
L	0.0347 ±0.008	0.881 ±0.203
L1	0.055 ±0.008	1.397 ±0.203
S	0.026(MAX)	0.660 (MAX)
y	0.004(MAX)	0.101(MAX)
Θ	0° -10°	0° -10°



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[illegible]

UNIT SYMBOL	INCH(BASE)	MM(REF)
A	0.047 (MAX)	1.20 (MAX)
A1	0.004 ±0.002	0.10 ±0.05
A2	0.039 ±0.002	1.00 ±0.05
b	0.008 + 0.002 - 0.001	0.20 + 0.05 - 0.03
c	0.005 (TYP)	0.127 (TYP)
D	0.724 ±0.004	18.40 ±0.10
E	0.315 ±0.004	8.00 ±0.10
e	0.020 (TYP)	0.50 (TYP)
HD	0.787 ±0.008	20.00 ±0.20
L	0.0197 ±0.004	0.50 ±0.10
L1	0.0315 ±0.004	0.08 ±0.10
y	0.003 (MAX)	0.076 (MAX)
Θ	0° 5°	0° 5°



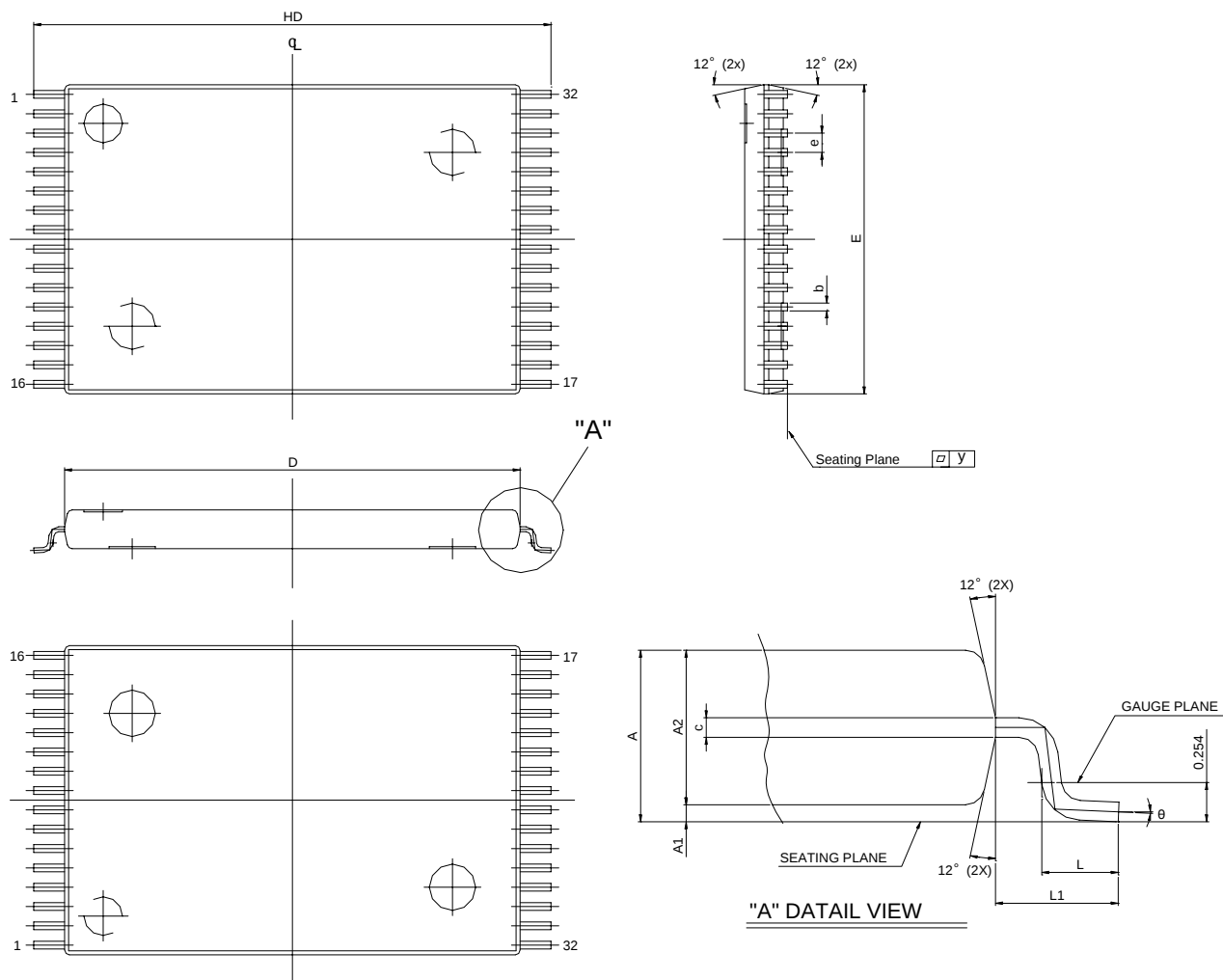
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128K X 8 BIT LOW POWER CMOS SRAM

32 pin 8mm x 13.4mm STSOP Package Outline Dimension



SYMBOL \ UNIT	INCH(BASE)	MM(REF)
A	0.049 (MAX)	1.25 (MAX)
A1	0.005 ±0.002	0.130 ±0.05
A2	0.039 ±0.002	1.00 ±0.05
b	0.008 ±0.01	0.20±0.025
c	0.005 (TYP)	0.127 (TYP)
D	0.465 ±0.004	11.80 ±0.10
E	0.315 ±0.004	8.00 ±0.10
e	0.020 (TYP)	0.50 (TYP)
HD	0.528±0.008	13.40 ±0.20.
L	0.0197 ±0.004	0.50 ±0.10
L1	0.0315 ±0.004	0.8 ±0.10
y	0.003 (MAX)	0.076 (MAX)
θ	0° 5°	0° 5°



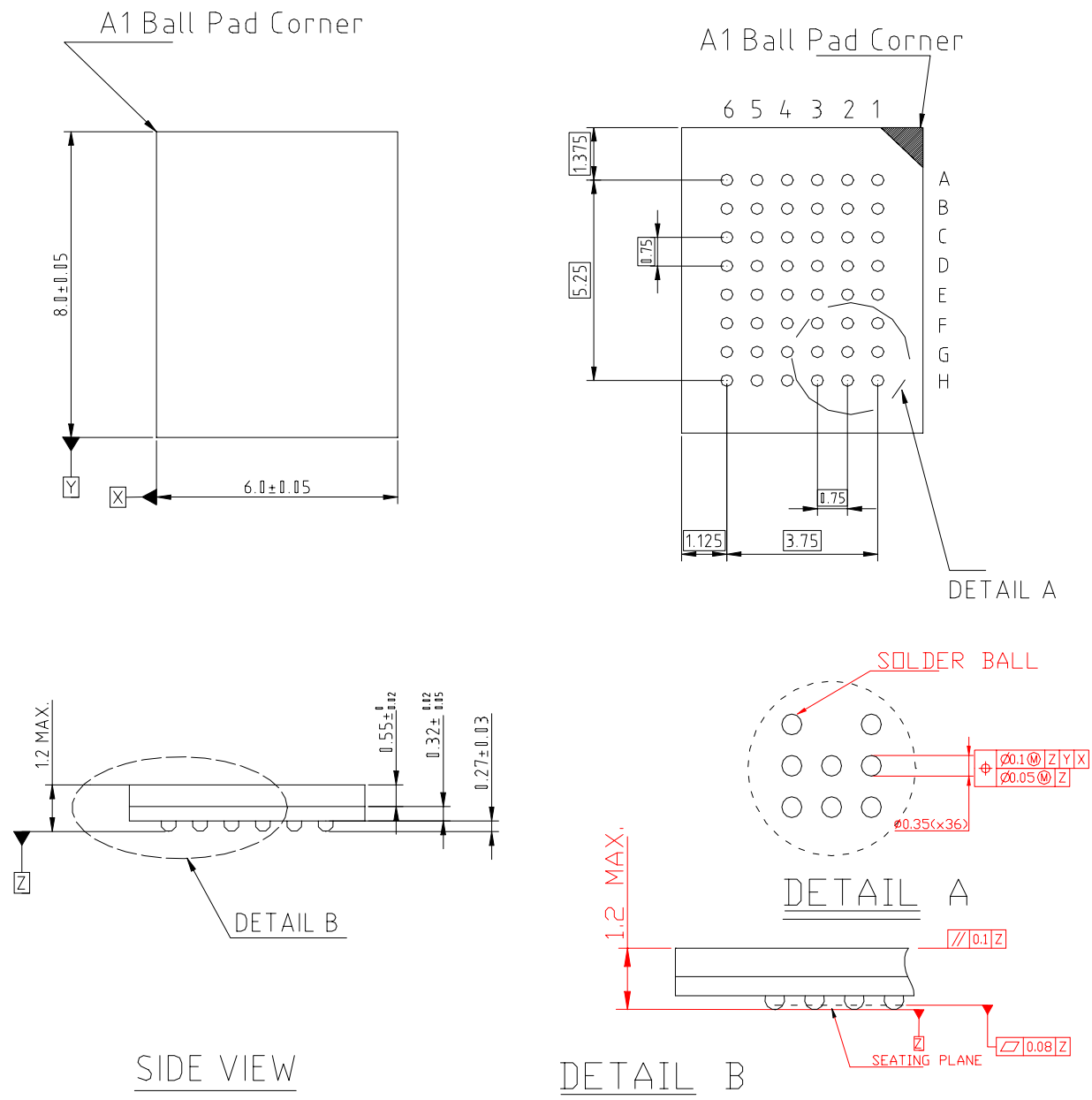
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36 pin 6mm×8mm TFBGA Package Outline Dimension





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128K X 8 BIT LOW POWER CMOS SRAM

ORDERING INFORMATION**INDUSTRIAL TEMPERATURE**

PART NO.	ACCESS TIME (ns)	STANDBY CURRENT (μ A) TYP.	PACKAGE
UT62L1024SC-55LI	55	20	32 PIN SOP
UT62L1024SC-55LLI	55	2	32 PIN SOP
UT62L1024SC-70LI	70	20	32 PIN SOP
UT62L1024SC-70LLI	70	2	32 PIN SOP
UT62L1024LC-55LI	55	20	32 PIN TSOP-I
UT62L1024LC-55LLI	55	2	32 PIN TSOP-I
UT62L1024LC-70LI	70	20	32 PIN TSOP-I
UT62L1024LC-70LLI	70	2	32 PIN TSOP-I
UT62L1024LS-55LI	55	20	32 PIN STSOP
UT62L1024LS-55LLI	55	2	32 PIN STSOP
UT62L1024LS-70LI	70	20	32 PIN STSOP
UT62L1024LS-70LLI	70	2	32 PIN STSOP
UT62L1024BS-55LI	55	20	36 PIN TFBGA
UT62L1024BS-55LLI	55	2	36 PIN TFBGA
UT62L1024BS-70LI	70	20	36 PIN TFBGA
UT62L1024BS-70LLI	70	2	36 PIN TFBGA

ORDERING INFORMATION (for lead free product)**INDUSTRIAL TEMPERATURE**

PART NO.	ACCESS TIME (ns)	STANDBY CURRENT (μ A) TYP.	PACKAGE
UT62L1024SCL-55LI	55	20	32 PIN SOP
UT62L1024SCL-55LLI	55	2	32 PIN SOP
UT62L1024SCL-70LI	70	20	32 PIN SOP
UT62L1024SCL-70LLI	70	2	32 PIN SOP
UT62L1024LCL-55LI	55	20	32 PIN TSOP-I
UT62L1024LCL-55LLI	55	2	32 PIN TSOP-I
UT62L1024LCL-70LI	70	20	32 PIN TSOP-I
UT62L1024LCL-70LLI	70	2	32 PIN TSOP-I
UT62L1024LSL-55LI	55	20	32 PIN STSOP
UT62L1024LSL-55LLI	55	2	32 PIN STSOP
UT62L1024LSL-70LI	70	20	32 PIN STSOP
UT62L1024LSL-70LLI	70	2	32 PIN STSOP
UT62L1024BSL-55LI	55	20	36 PIN TFBGA
UT62L1024BSL-55LLI	55	2	36 PIN TFBGA
UT62L1024BSL-70LI	70	20	36 PIN TFBGA
UT62L1024BSL-70LLI	70	2	36 PIN TFBGA



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